

1310nm FP LD Module for OTDR

Features

High optical output power

Emission wavelength is in 1.3μm band

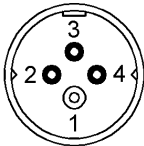
MQW active layer

Applications

OTDR



PIN assignment



F type	
1	LD(+)/case
2	LD(-)
3	-
4	-

This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures



LASER RADIATION
AVOID EXPOSURE TO BEAM
Class 3 B laser product



CAUTION
STATIC SENSITIVE DEVICE
OBSERVE PRECAUTIONS

Absolute maximum ratings

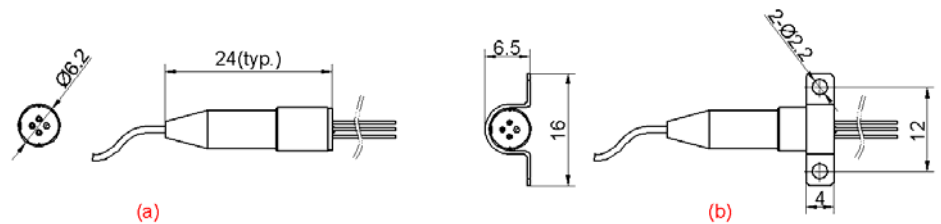
Parameter	Symbol	Min.	Max.	Unit	Test condition
Storage temperature	Tst	-40	+70	°C	-
Operating temperature	Top	-40	+85	°C	-
Reverse voltage	V _R		2	V	CW
Solder temperature/time			260/10	°C /S	-

Optical & electrical characteristics(T=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Center wavelength	λ _c	1290	1310	1330	nm	-
Threshold current	I _{th}	-	30	50	mA	
Spectral width	Δλ	-	-	10	nm	I _{th} +20mA,-20dB
Operating current	I _{op}	400	700	900	mA	
Output power	P	80	-	-	mW	I _{op} ,pulse①
Operating voltage	V _{op}	-	-	5	V	CW,I _{th} +20mA
Rise/ Fall time	T _r /T _f	-	1	2	nS	10%~90%,I _b =I _{th}

Note: ①Pulse condition:Pulse width≤ 10us,Duty ratio≤1%

Dimensions Diagram



Order information

SLOT	XX	XX
	wavelength	Connect
	31,1310	FC:FC/PC
	55,1550	SC:SC/PC
		SP,specify

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